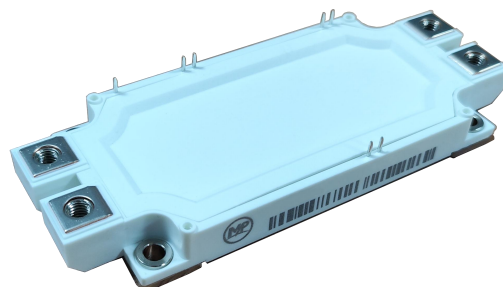


Electrical Features

- Trench/Fieldstop IGBT
- Low $V_{CE(sat)}$
- $V_{CE(sat)}$ with positive temperature coefficient
- 10 μ s short circuit capability
- Fast&soft reverse recovery anti-parallel FWD
- Low inductance case



Typical Applications

- Motor Drives
- High Power Converters
- UPS System
- Servo Drives
- Wind Turbines

IGBT, Inverter

Maximum Rated Values							
Symbol	Item	Conditions		Rating		Unit	
IGBT							
V _{CES}	Collector-emitter voltage	T _{vj} =25°C		1200		V	
V _{GES}	Gate-emitter voltage	-		±20		V	
I _C	Collector current,DC	T _C =100°C,T _{vj} =175°C		600		A	
I _{CRM}	Repetitive peak collector current	t _p =1ms		1200		A	
t _{SC}	Short circuit withstand time	V _{GE} =15V, V _{CC} =600V, T _{vj} ≤150°C		10		μs	
P _{tot}	Total power dissipation	T _C =25°C,T _{vj} =175°C		4838		W	
Characteristics Values							
Symbol	Item	Conditions		Values			Unit
IGBT				Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =1200V,V _{GE} =0V,T _{vj} =25°C		-	-	3	mA
I _{GES}	Gate leakage current	V _{CE} =0V,V _{GE} =20V,T _{vj} =25°C		-	-	400	nA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =23mA,V _{CE} =V _{GE} ,T _{vj} =25°C		5.0	5.7	7.0	V
V _{CESat}	Collector-emitter saturation voltage	I _C =600A V _{GE} =15V	T _{vj} =25°C	-	2.2	2.4	
			T _{vj} =125°C	-	2.7	-	
			T _{vj} =150°C	-	2.9	-	
C _{ies}	Input capacitance	V _{CE} =25V,V _{GE} =0V f=1MHz,T _{vj} =25°C		-	49.77	-	nF
C _{oes}	Output capacitance			-	2.28	-	
C _{res}	Reverse transfer capacitance			-	2.22	-	
Q _G	Gate charge	V _{GE} =± 15V		-	7.5	-	nC
R _g	Internal gate resistance	T _{vj} =25°C		-	0.28	-	Ω

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$, $I_C=600A$, $V_{GE}=\pm 15V$, $R_{G(on)}=5.1\ \Omega$, $R_{G(off)}=5.1\ \Omega$, $L_{load}=200uH$	$T_{vj}=25^{\circ}C$	-	272	-	ns
			$T_{vj}=125^{\circ}C$	-	253	-	
			$T_{vj}=150^{\circ}C$	-	249	-	
t_r	Rise time		$T_{vj}=25^{\circ}C$	-	264	-	
			$T_{vj}=125^{\circ}C$	-	262	-	
			$T_{vj}=150^{\circ}C$	-	259	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^{\circ}C$	-	1019	-	
			$T_{vj}=125^{\circ}C$	-	1096	-	
			$T_{vj}=150^{\circ}C$	-	1112	-	
t_f	Fall time		$T_{vj}=25^{\circ}C$	-	144	-	
			$T_{vj}=125^{\circ}C$	-	195	-	
			$T_{vj}=150^{\circ}C$	-	225	-	
E_{on}	Turn-on energy (per pulse)		$T_{vj}=25^{\circ}C$	-	148.5	-	mJ
			$T_{vj}=125^{\circ}C$	-	159.4	-	
			$T_{vj}=150^{\circ}C$	-	166.9	-	
E_{off}	Turn-off energy (per pulse)		$T_{vj}=25^{\circ}C$	-	83.9	-	
			$T_{vj}=125^{\circ}C$	-	95.6	-	
			$T_{vj}=150^{\circ}C$	-	99.3	-	
R_{thJC}	Thermal resistance,junction to case	per IGBT		-	-	0.031	K/W
R_{thCH}	Thermalresistance,case to heatsink	per IGBT/ $\lambda_{grease}=1W/(m\cdot K)$		-	0.035	-	K/W
T_{vjop}	Temperature under switching conditions			-40		150	$^{\circ}C$

Diode, Inverter**Maximum Rated Values**

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V
I_F	Forward current, DC	$T_C=100^\circ C, T_{vj}=150^\circ C$	600	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	1200	A

Characteristic Values

V _F	Continuous forward voltage	I _F =600A V _{GE} =0V	T _{vj} =25°C	-	2.28	-	V
			T _{vj} =125°C	-	2.51	-	
			T _{vj} =150°C	-	2.53	-	
I _{RM}	Peak reverse recovery current	V _R =600V I _F =600A V _{GE} =-15V	T _{vj} =25°C	-	159.5	-	A
			T _{vj} =125°C	-	228.4	-	
			T _{vj} =150°C	-	249.4	-	
t _{rr}	Reverse recovery time		T _{vj} =25°C	-	516.1	-	ns
			T _{vj} =125°C	-	475.9	-	
			T _{vj} =150°C	-	474.5	-	
Q _r	Recovered charge		T _{vj} =25°C	-	35.1	-	μC
			T _{vj} =125°C	-	55.8	-	
			T _{vj} =150°C	-	66.5	-	
E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	9.9	-	mJ
			T _{vj} =125°C	-	18.9	-	
			T _{vj} =150°C	-	21.9	-	

R_{thJC}	Thermal resistance, junction to case	per diode	-	-	0.071	K/W
R_{thCH}	Thermal resistance, case to heatsink	per diode/ $\lambda_{grease}=1\text{ W/(m}\cdot\text{K)}$	-	0.0395	-	K/W
T_{vjop}	Temperature under switching conditions		-40		150	°C

NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R_{25}	Rated resistance	$T_C=25^\circ\text{C}$	-	5	-	k Ω
$\Delta R/R$	Deviation of resistance	$T_C=100^\circ\text{C}, R_{100}=493\Omega$	-5	-	5	%
P_{25}	Power dissipation	$T_C=25^\circ\text{C}$	-	-	20	mW
$B_{25/50}$	B-constant	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$	-	3375	-	K
$B_{25/80}$	B-constant	$R_2=R_{25}\exp[B_{25/80}(1/T_2-1/(298.15\text{K}))]$	-	3411	-	
$B_{25/100}$	B-constant	$R_2=R_{25}\exp[B_{25/100}(1/T_2-1/(298.15\text{K}))]$	-	3433	-	

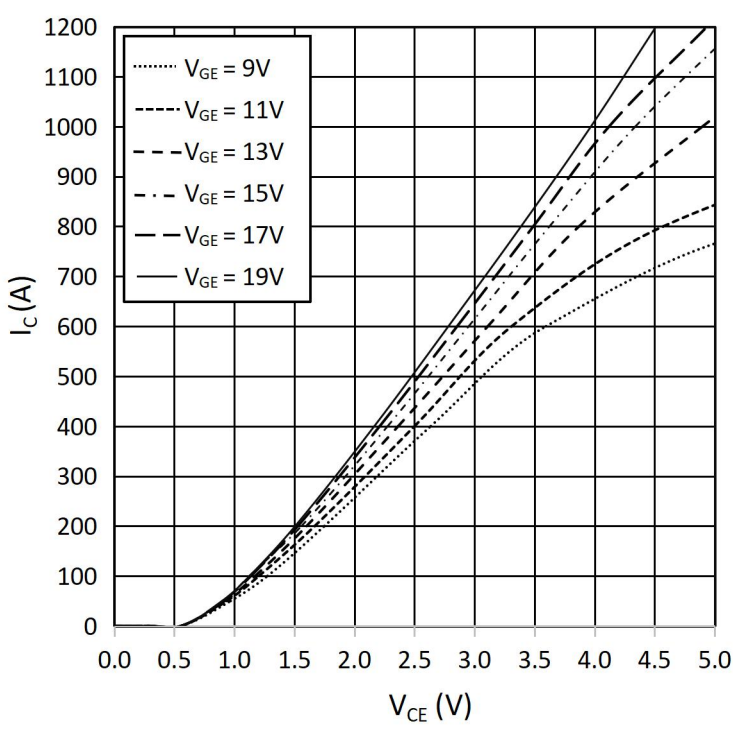
Module

Symbol	Item	Conditions	Rating			Unit
V_{ISOL}	Isolation voltage	Terminals to baseplate, RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500			V
-	Material of module baseplate	-	Cu			-
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al_2O_3			-
T_{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	13	-	mm
		Terminal to base plate	-	14.5	-	
da	Clearance	Terminal to terminal	-	10	-	mm
		Terminal to base plate	-	12.5	-	
m	Weight	-	-	340	-	g

output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$

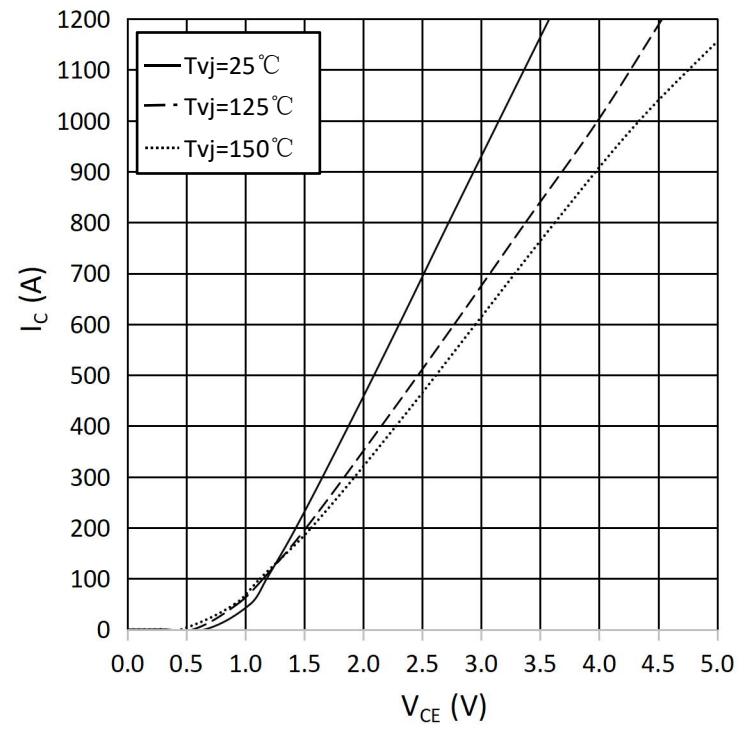
$T_{vj} = 150^{\circ}\text{C}$



output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$

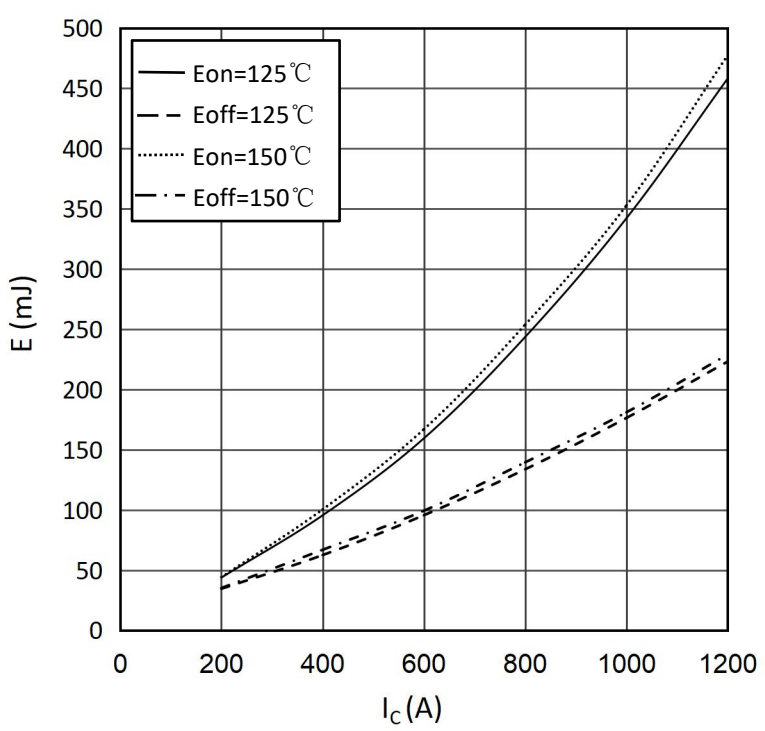
$V_{GE} = 15\text{ V}$



switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$

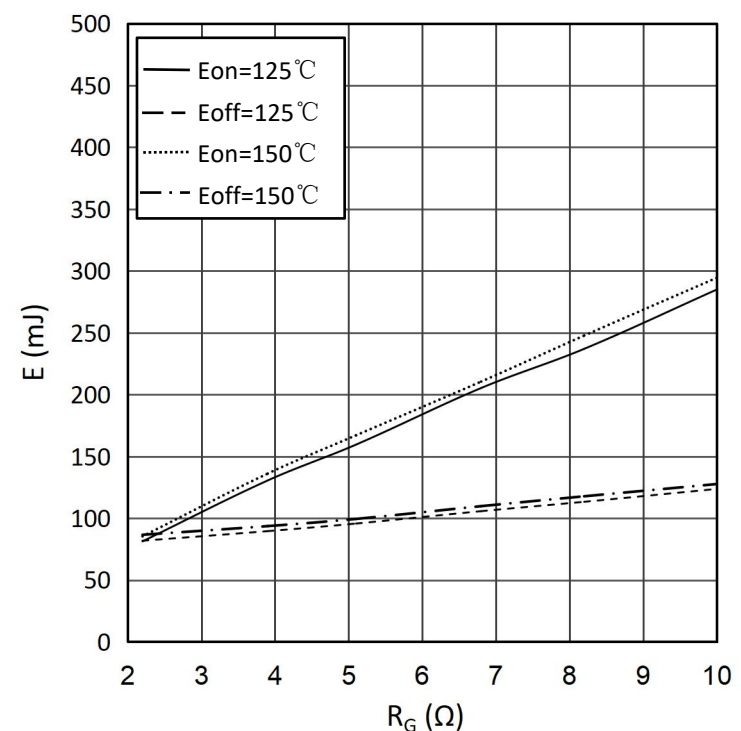
$V_{GE} = \pm 15\text{V}$, $R_{Gon} = 5.1\Omega$, $R_{Goff} = 5.1\Omega$, $V_{CE} = 600\text{V}$



switching losses IGBT, Inverter (typical)

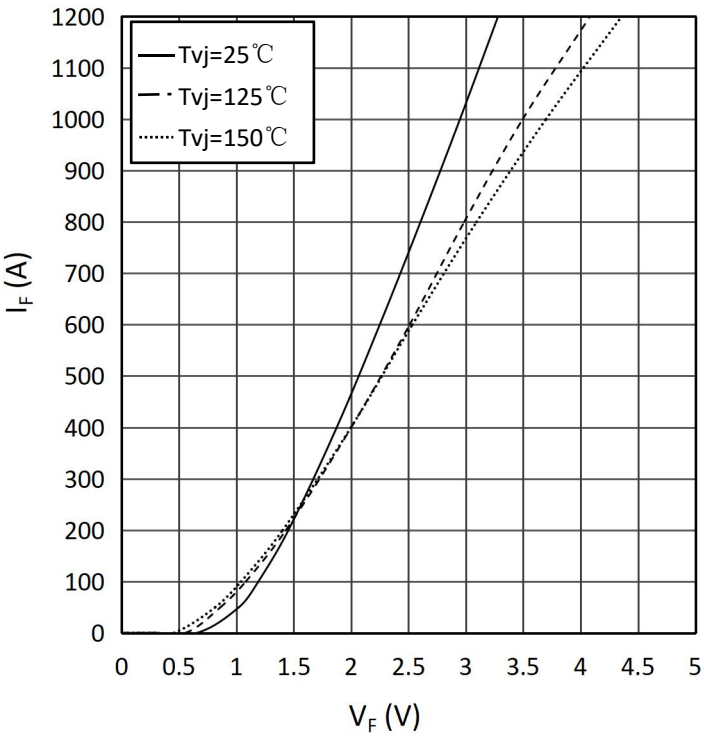
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$

$V_{GE} = \pm 15\text{V}$, $I_C = 600\text{A}$, $V_{CE} = 600\text{V}$



forward characteristic of Diode, Inverter (typical)

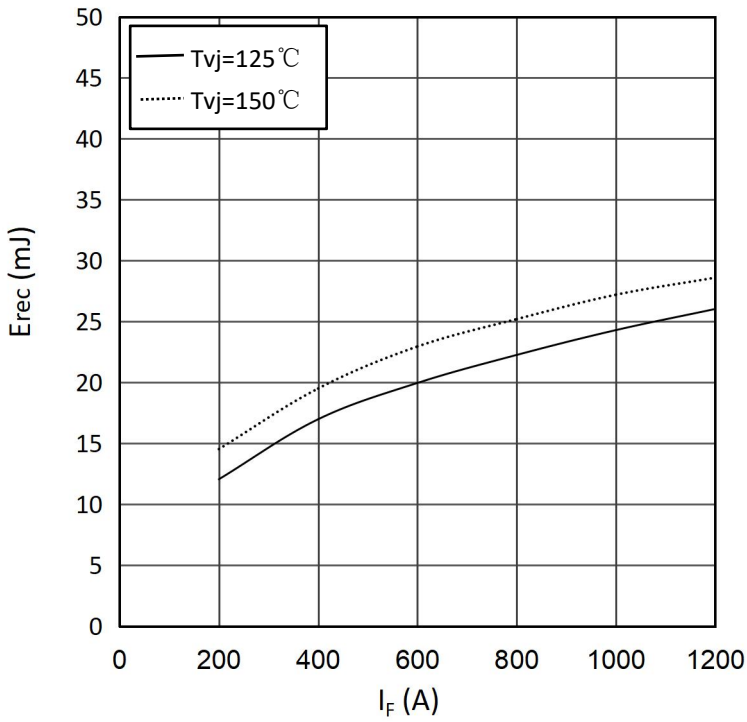
$I_F = f(V_F)$



switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$

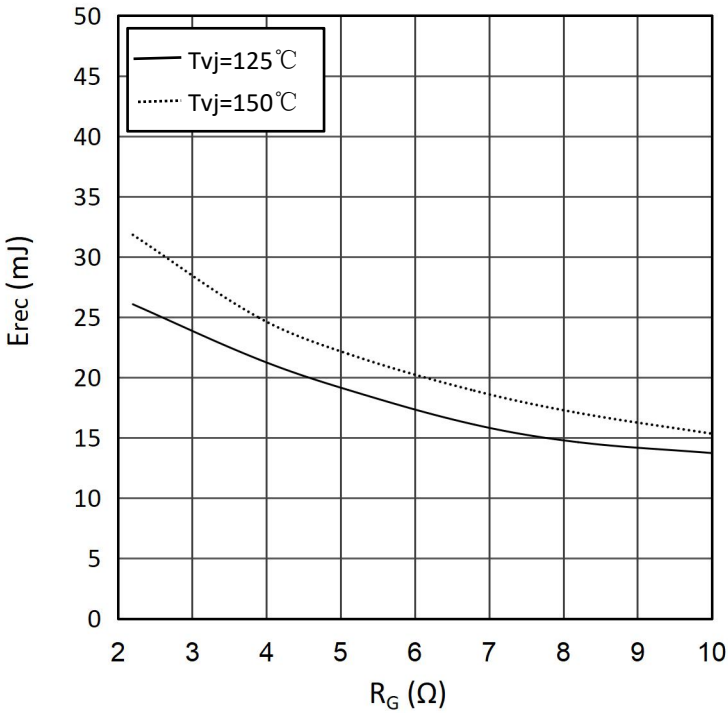
$R_{Gon}=5.1\Omega, V_{CE}=600V$



switching losses Diode, Inverter (typical)

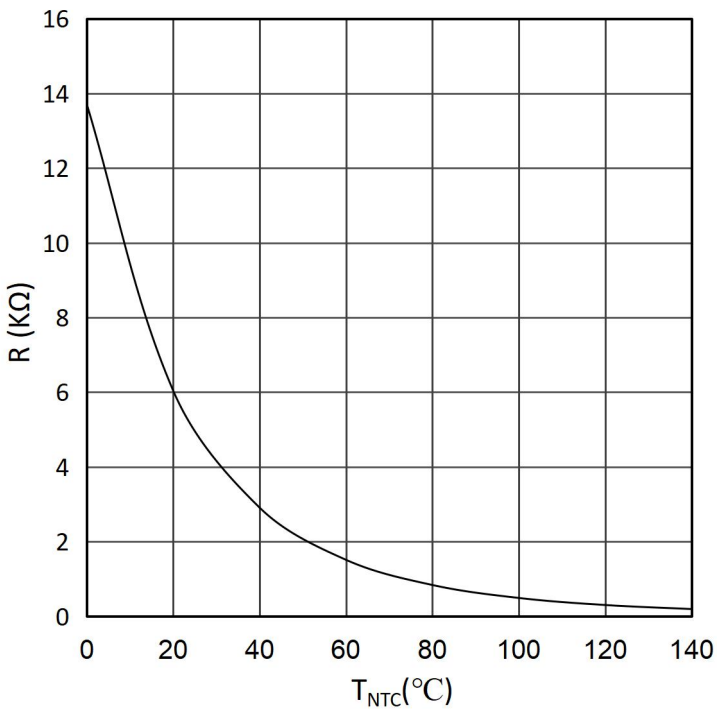
$E_{rec} = f(R_G)$

$I_F=600A, V_{CE}=600V$

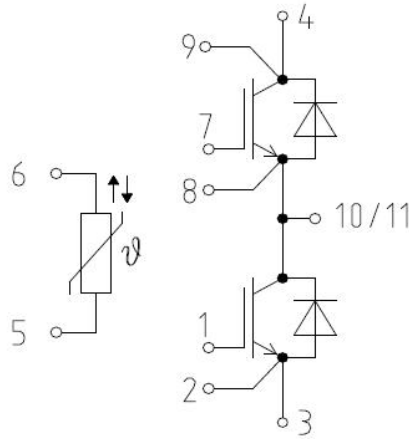


NTC-Thermistor-temperature characteristic(typical)

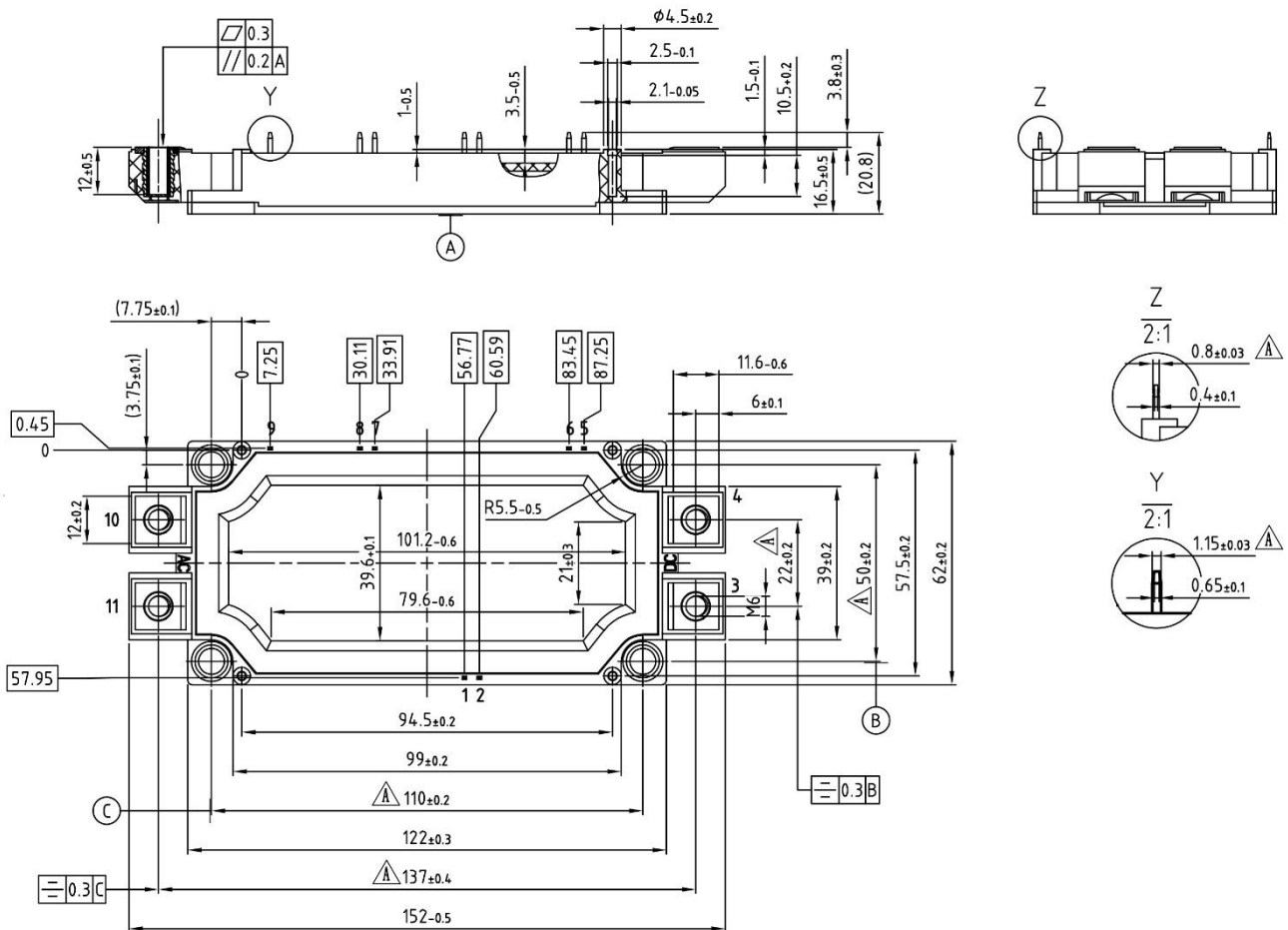
$R=f(T)$



Circuit diagram headline



Package outlines (Unit: mm)



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